4. Marking

Table 4. Marking

Type number	Marking	Description
BFU630F	D2*	* = p : made in Hong Kong
		* = t : made in Malaysia
		* = w : made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	16	V
V_{CEO}	collector-emitter voltage	open base		-	5.5	V
V_{EBO}	emitter-base voltage	open collector		-	2.5	V
I_C	collector current			-	30	mA
P_{tot}	total power dissipation	T_{sp} Ω 90 ∀C	[1]	-	200	mW
T_{stg}	storage temperature			465	+150	∀C
T_j	junction temperature			-	150	∀C

[1] T_{sp} is the temperature at the solder point of the emitter lead.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		300	K/W

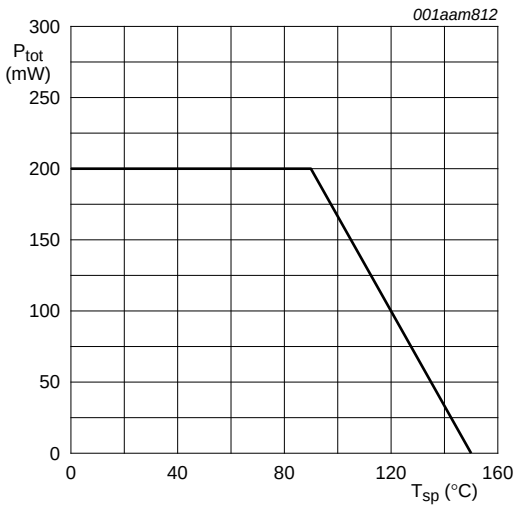

Fig 1. Power derating curve

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